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Table of Contents

Carbon Nanotubes in Electronics.....	1
<i>Siegmar Roth, Jiangling Wang, Viera Skakalova</i>	
Superior nMOSFET scalability using Fluorineine co-implantation and spike annealing.....	7
<i>S. Kubicek, T. Hoffmann, E. Augendre, B. Pawlak, T. Chiarella, C. Kerner, S. Severi, A. Falepin, A. De Keersgieter, T.Noda, M. Jurczak, P. Absil, S. Biesemans</i>	
Formation of sharp-apex pyramids for active tips used in scanning probe microscopy	11
<i>J. Soltys, D. Gregusova, R. Kudela, A. Satka, I. Kostic, V. Cambel</i>	
RF characterization and modeling of AlGaN/GaN based HFETs and MOSHFETs	15
<i>A. Fox, M. Marso, G. Heidelberger, P. Kordoi</i>	
Electronic transport in carbon nanotubes: From individual nanotubes to thin and thick networks.....	19
<i>V. Skákalová, A. B. Kaiser, Y.-S. Woo, S. Roth</i>	
Electron-electron Interaction Induced Parabolic Negative Magnetoresistance in Two-dimensional Electron Gas in InGaAs/InP	22
<i>B. Podör, G. Reményi</i>	
Terahertz-Radiation Photomixers on Nitrogen-Implanted GaAs	26
<i>M. Mikulics, M. Marso, S. Stancek, E. A. Michael, P. Kordoi</i>	
Simulation of Advanced Tunneling Devices	30
<i>A. Heigl, G. Wachutka</i>	
Simulation of the p-type RTD	34
<i>J. Voves</i>	
Investigation of Si delta-doped InGaAs/GaAs QW MSM photodetectors.....	38
<i>M. Florovic, J. Kovác, R. Srnánek, J. Jakabovic, J. Chovan, B. Sciana, D. Radziewicz, M. Tlaczala</i>	
Micro-Raman scattering: A versatile tool for characterization of semiconductor structures	42
<i>G. Irmer</i>	
Measurement of the Germanium fraction in strained and relaxed SiGe by Spectroscopic Ellipsometry	48
<i>J. Moers, D.M. Buca, M. Goryll, R. Loo, M. Caymax, S. Mantl</i>	
X-ray diffraction characterization of Low Temperature grown GaAs/InP epilayers	52
<i>C. Ferraria, F. Dubeckyb, R. Kudelab, J. Johnc, R. Srnanekd</i>	
Investigation of Nickel Silicide Contact Layers for Power Diodes	56
<i>A. -atka, R. Srnánek, A. Vincze, D. Donoval, G. Irmer, J. Ková</i>	
Reliability issues in advanced High k/metal gate stacks for 45 nm CMOS applications.....	60
<i>G. Groeseneken, M. Aoulaiche, S. De Gendt, R. Degraeve, M. Houssa, T. Kauerauf, L. Pantisano</i>	
Nb-Ti/Al/Ni/Au Ohmic Metallic System to AlGaN/GaN.....	65
<i>T. Lalinsky, G. Vanko, Z. Mozolova, J. Liday, P. Vogrincic, A. Vincze, F. Uherek, Hascik, I. Kostic</i>	
Electrical and optical behaviour of nanocrystalline CdS/InP heterojunction p-n diodes	69
<i>V. Rakovics, Zs. J. Horváth, B. Podör</i>	
High Purity p-type InP Grown by LPE with Rare-Earth Admixtures	70
<i>J. Grym, O. Procházková, J. Zavadil, K. Zdánský</i>	
Performance study of bulk semi-insulating InP radiation detectors with different electrode metallizations.....	74
<i>B. Zatkova, F. Dubeckyá, O. Procházková, V. Necasc</i>	
GaAs and GaN based SAW chemical sensors: acoustic part design and technology.....	78
<i>L. Rufer, T. Lalinsky, D. Grobelny, S. Mir, G. Vanko, Zs. Oszi, Z. Mozolova, J. Gregu</i>	
Physical properties of transparent conductive oxides prepared by RF reactive sputtering	82
<i>V. Tvarozek, I. Novotny, P. Sutta, S. Flickyngrova, L. Harmatha, E. Vavrinsky, M. Nigrovicova, J. Mullerova</i>	

Table of Contents

Translinear Subthreshold MOS Filter for the Wireless Sensors Applications.....	86
<i>Adam Boura, Miroslav Husak</i>	
Direction Sensitivity Matrix with PLL Temperature Sensor.....	90
<i>M. Husak, A. Boura, J. Jakovenko</i>	
Differential blood analysis by thin film interdigitated arrays of electrodes	94
<i>R. Viglaský, M. Nigrovicová, V. Tvarožek, M. Weis</i>	
Influence of the doping material on the benzene detection	98
<i>P. Ivanov, F. Blanco, I. Gracia, N. Sabaté, X. Vilanova, X. Correig, L. Fonseca, E. Figueras, J. Santander, R. Rubio, C. Cané</i>	
Design and simulation of humidity micro-sensors structure based on Polymers.....	102
<i>Pavel Suchánek, Miroslav Husák</i>	
4H-SiC Diode with a RuOx and a RuWOx Schottky Contact Irradiated by Fast Electrons	106
<i>L. Stuchlíková, L. Harmatha, D. Búč, J. Benkovská, B. Hlinka, G. G. Siu</i>	
Rapid thermal annealing and performance of Al₂O₃/GaN metaloxide-semiconductor structures	110
<i>K. Cico, J. Kuzmík, D. Gregusová, T. Lalinsky, A. Georgakilas, D. Pogany, K. Frohlich</i>	
Helium Irradiation for Advanced Lifetime Control in Silicon: New Recombination Centers and Their Interaction Stimulated by Isochronal Annealing.....	114
<i>Volodymyr Komarnitskyy, Pavel Hazdra</i>	
Electrical and Memory Properties of Non-volatile Memory Structures with Embedded Si Nanocrystals.....	118
<i>Zs. J. Horváth, P. Basa, T. Jászi, A. E. Pap, P. Szöllősi, K. Nagy, V. Hardy</i>	
Leakage current and Physical properties of Tantalum oxide thin films for Micro capacitor integration.....	122
<i>Insung-Kim, Jaesung-Song, Bokki-Min</i>	
Leakage characteristics of advanced MOS capacitors with hafnium silicate dielectric and Ru electrode	126
<i>M. Tapajna, K. Huieková, K. Fröhlich, E. Dobrocka, F. Roozeboom</i>	
First results observed with test X-CT system using GaAs radiation detector working in single photon counting regime.....	130
<i>F. Dubecký, B. Zatko, I. Frollo, J. Juras, J. Pribil, J. Jakubek, J. Mudron</i>	
Changes of GaAs neutron detectors properties after fast neutron irradiation.....	134
<i>Milan Ladziansky, Andrea Sagatova-Perdochova, Bohumir Zatko, Vladimir Necas, Frantisek Dubecky</i>	
Control of defects and impurities at GaN and AlGaN surfaces for FET and sensor applications	138
<i>Junji Kotani, Masamitsu Kaneko, Kazushi Matsuo, Tamotsu Hashizume</i>	
Comparison of AlGaN/GaN MSM varactor diodes based on HFET and MOSHFET layer structures	146
<i>M. Marso, A. Fox, G. Heidelberger, P. Kordoi, H. Lüth</i>	
Dark current of AlGaAs/GaAs n-QWIP prepared on patterned (001) GaAs substrate by MOVPE.....	150
<i>Strichovanec P., Kudela R., Vávra I., R. Srnánek, Novák J.</i>	
Study of electrically active defects in GaAs/InAs/GaAs QDs structures by DLTS and TEM.....	154
<i>M. Prezioso, E. Gombia, R. Mosca, L. Nasi, A. Motta, P. Frigeri, G. Trevisi, L. Seravalli, S. Franchi</i>	
Technology related issues regarding fabrication of AlGaN/GaN-based MOSHFETs with GdScO₃ as dielectric	158
<i>G. Heidelberger, M. Roeckerath, R. Steins, M. Stefaniak, A. Fox, J. Schubert, N. Kaluza, M. Marso, H. Lüth, P. Kordoi</i>	
Investigation of GaN/ ZnO heterostructures properties	162
<i>J. Kovac, J. Skriniarova, P. Kudela, I. Novotny, J. Bruncko, D. Donoval, J. Jakabovic, M. Michalka, L. Janos, A. sVincze, D. Hasko</i>	

Table of Contents

Preparation and properties of AlGaN/GaN MOSFETs with MOCVD Al₂O₃ as gate oxide.....	166
<i>R. Stoklas, K. Cico, D. Greguiová, J. Novái, P. Kordoi</i>	
Post-metallization H₂ annealing of electrically active defects in Ta₂O₅/nitrided Si stacks	170
<i>A. Paskaleva, E. Atanassova</i>	
2D electron transport through potential barrier prepared by LAO on shallow GaAs/Al_xGa_{1-x}As/InGaP heterostructure.....	174
<i>J. Martaus, V. Cambel, R. Kudela, D. Gregusova, J. Soltys</i>	
Recent Developments in Microsystem- and Nanodevice-TCAD.....	178
<i>Gerhard Wachutka</i>	
Analysis of device geometry on the ruggedness of power DMOS transistor supported by 3-D modeling and simulation	180
<i>Andrej Vrbicky, Daniel Donoval, Juraj Marek, Ales Chvala, Peter Beno</i>	
New 600V Lateral Superjunction Power MOSFETs Based on Embedded Non-Uniform Column Structure	184
<i>K. Permethammasin, G. Wachutka, M. Schmitt, H. Kapels</i>	
FEM Simulation and Characterization of Microcantilevers Resonators.....	188
<i>Margarita S. Narducci, Eduard Figueras, Isabel Garcia, Luís Fonseca, Carles Cané</i>	
Electric energy harvesting inside self powered microsystem	192
<i>Janicek Vladimir, Husak Miroslav</i>	
Monitoring of Psychosomatic Properties of Human Body by Skin Conductivity Measurements using Thin Film Microelectrode Arrays	196
<i>E. Vavrinský, V. Stopjaková, L. Majer, V. Tvarožek, M. Weis, P. Marman</i>	
PREPARATION AND CHARACTERIZATION OF MICROHOTPLATE FOR GAS SENSORS	200
<i>A. Reháková, D. Tengeri, I. Hotový, T. Lalinský, V. Veháek, L. Spiess, H. Romanus, Š. Hašík</i>	
Reduced-order modeling of capacitive MEMS microphones using mixed-level simulation	204
<i>M. Niessner, W. Bedyk, G. Schrag, G. Wachutka, B. Margesin, A. Faes</i>	
Recent Advances in Organic Electronic.....	208
<i>J. Kovác, J. Jakabovic, L. Peternai, O. Lengyel, M. Kytká</i>	
Energy Band Diagram of the Ru/Hf0.75Si0.25Oy/Si Gate Stack	216
<i>K. Fröhlich, J. P. Espinos, M. Tapajna, K. Huieková, R. Lupták</i>	
Towards a Microtechnology based 4-channel infrared detector unit for a miniaturised NDIR system	220
<i>L. Fonseca, J. Santander, R. Rubio, N. Sabaté, P. Ivanov, E. Figueras, I. Gràcia, C. Cané</i>	
Nano-structures for light management in optoelectronic devices.....	224
<i>M. Zeman, J. Krc</i>	
Preparation of p-type ZnO thin films by RF diode sputtering	228
<i>K. Shtereva, I. Novotny, V. Tvarozek, R. Srnanek, J. Kovac, P. Sutta</i>	
Coupling Capacitances of Connecting-lead Systems in Integrated Circuits	234
<i>J. Novak, J. Foit, V. Janicek</i>	
The Effect of Rapid Thermal Annealing on Oxygen Precipitation in Nitrogen Doped Silicon Substrate	238
<i>L. Stuchlíková, L. Harmatha, M. Tapajna, P. Ballo, P. Písecný, M. Benkovic, J. Jakabovic</i>	
Microstructure of HfO₂ and HfxSi1-xOy Dielectric Films Prepared on Si for Advanced CMOS Application	242
<i>M. Franta, A. Rosová, M. Tapajna, E. Dobrocka, K. Fröhlich</i>	
Deep Defects in MOVPE Grown SiC/AlGaN/GaN Heterostructures	246
<i>D. Kindl, P. Hubik, J. Kri.tofik, J. J. Mare, Z. Vyborny, M. R. Leys, S. Boeykens</i>	
Diagnostics of LT GaAs/ InP structures by micro-Raman spectroscopy.....	250
<i>R. Srnánek, G. Irmer, R. Záluský, F. Dubeczký, R. Kúdela, A. Vincze, I. Novotný, J. John</i>	

Table of Contents

RF plasma deposition of thin amorphous silicon carbide films using a combination of silan and methane.....	254
<i>J. Huran, I. Hotový, J. Pezoldt, N. I. Balalykin, A.P. Kobzev</i>	
Photoluminescence and electrical characterization of transparent Eu and Pd-doped TiO₂ thin films	258
<i>J. Domaradzki, A. Borkowska, D. Kaczmarek</i>	
Structural, optical and electrical properties of nanocrystalline TiO₂ – HfO₂ thin films	262
<i>J. Domaradzki, D. Kaczmarek</i>	
Microelectromagnetic matrix for local assembling of magnetic nanoparticles	266
<i>S. Luby, L. Chitu, E. Majkova, R. Senderak, I. Kostic, P. Hrkut, L. Matay, S. Hascik, T. Lalinsky, I. Capek, A. Satka</i>	
Nickel ohmic contact on silicon carbide.....	270
<i>Machac P., Barda B., Sajdl P.</i>	
Two-dimensional electron gas as the THz radiation detector	274
<i>Michal Horák</i>	
Influence of mechanical strain on essential characteristics of GMR	
structures	278
<i>V. Áć, B. Anwarzai, S. Luby, E. Majkova</i>	
Energy band diagram and charge distribution in AlGaN/GaN heterostructure studied by classical approach	282
<i>J. Osvald</i>	
Spectroscopic ellipsometric study of LPCVD-deposited Si nanocrystals in SiNx and Si₃N₄.....	286
<i>P. Basa, P. Petrik, M. Fried</i>	
Annealing behaviour of low temperature grown GaAs investigated by SIMS.....	289
<i>A. Vincze, J. Kováč, R. Srnánek</i>	
Evaluation of parameters of Schottky junctions with large excess currents	293
<i>Zs. J. Horváth</i>	
Deposition of AZ5214-E Layers on Non-planar Substrates with a "Draping" Technique	294
<i>P. Eliáí, D. Greguiová, P. Strichovanec, I. Kostic, J. Novák</i>	